

## LOW VOLTAGE NPN POWER TRANSISTOR

PRELIMINARY DATA

### **Features**

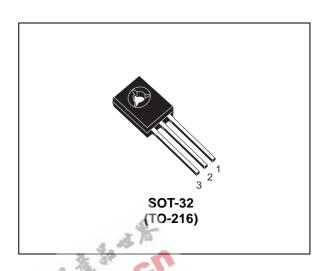
■ LOW SATURATION VOLTAGE

### **Applications**

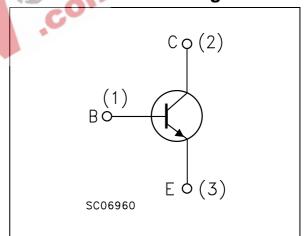
- SCANNING VELOCITY MODULATION IN CRT DISPLAYS
- MEDIUM POWER LINEAR AND SWITCHING APPLICATIONS

### **Description**

The ST600K is manufactured by low voltage Epitaxial Base technology and it is housed in SOT-32 plastic package. The complementary PNP type is ST631K.



### Internal Schematic Diagram



### **Order Codes**

Part Number	Marking	Package	Packing
ST600K	600K	SOT-32	TUBE

# 1 Absolute Maximum Ratings

Table 1. Absolute Maximum Rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)	120	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	120	V
V <sub>EBO</sub>	Collector-Base Voltage (I <sub>C</sub> = 0)	5	V
I <sub>C</sub>	Collector Current	1	А
I <sub>CM</sub>	Collector Peak Current (t <sub>P</sub> < 5ms)	2	А
I <sub>B</sub>	Base Current	0.5	А
I <sub>BM</sub>	Base Peak Current (t <sub>P</sub> < 5ms)	1	А
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25°C	12.5	W
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C
TJ	Max. Operating Junction Temperature	150	°C

Table 2. Thermal Data

Symbol	Parameter	7. 30	Value	Unit
R <sub>thJ-case</sub> R <sub>thJ-amb</sub>	Thermal Resistance Junction-Case Thermal Resistance Junction-Case	Max Max	10 100	°C/W

**ST600K** 2 Electrical Characteristics

## 2 Electrical Characteristics

Table 3.Electrical Characteristics ( $T_{CASE} = 25^{\circ}C$ ; unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 50V			1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 4V			1	μΑ
V <sub>(BR)CBO</sub> Note: 1	Collector-Base Breakdown Voltage (I <sub>E</sub> = 0)	$I_C = 10\mu A$	120			V
V <sub>(BR)CEO</sub> Note: 1	Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1 mA	120		1	V
V <sub>(BR)EBO</sub> Note: 1	Collector-Emitter Breakdown Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	120		1	V
V <sub>CE(sat)</sub> Note: 1	Collector-Emitter Saturation Voltage	$I_C = 500 \text{ mA}$ $I_B = 50 \text{ mA}$	1		0.5	V
V <sub>BE(sat)</sub> Note: 1	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}$ $I_B = 50 \text{ mA}$			1.2	V
h <sub>FE</sub> Note: 1	DC Current Gain	$I_C = 100 \text{ mA}$ $V_{CE} = 5 \text{ V}$ $V_{CE} = 5 \text{ V}$	120 50		280	
C <sub>CBO</sub>	Collector-Base Capacitance (I <sub>B</sub> = 0)	V <sub>CB</sub> = 10 V f=1MHz		40		pF
	INDUCTIVE LOAD	$I_C = 500 \text{ mA}$ $V_{CC} = 12V$				
t <sub>on</sub>	Turn-On Time	$I_{B1} = -I_{B2} = 50 \text{ mA}$ $t_p = 20 \mu \text{s}$		100		ns
t <sub>off</sub>	Turn-Off Time			500		ns
t <sub>s</sub>	Storage Time			800		ns

Note: 1 Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$ 1.5%.

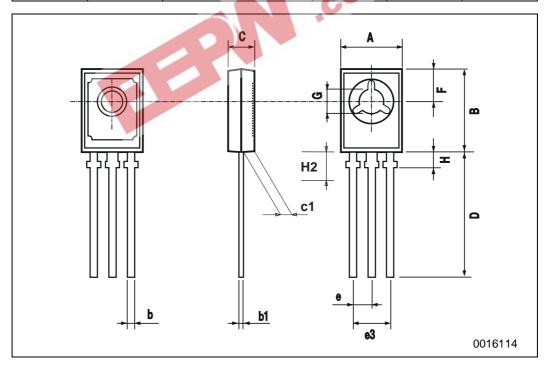
## 3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>



### **SOT-32 (TO-126) MECHANICAL DATA**

DIM.	mm			inch		
Di.W.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
С	2.4		2.7	0.040		0.106
c1	1.0		1.3	0.039		0.050
D	15.4		16.0	0.606		0.629
е		2.2			0.087	
e3	4.15		4.65	0.163	.0	0.183
F		3.8			0.150	
G	3		3.2	0.118	00	0.126
Н			2.54	3	10.	0.100
H2		2.15	133	. 0/1	0.084	



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4 Revision History

# 4 Revision History

Date	Revision	Changes
26-Jul-2005	1	Initial release.



ST600K 4 Revision History



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